Ordering number: EN3442

N-Channel Silicon MOSFET



2SK1439

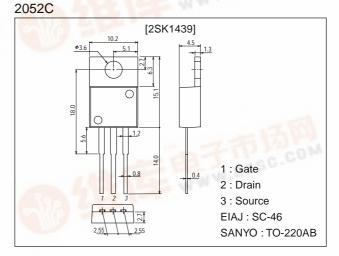
Ultrahigh-Speed Switching Applications

Features

- · Low ON-state resistance.
- · Ultrahigh-speed switching.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|------------------|------------------------|-------------|------|
| Drain-to-Source Voltage | V _{DSS} | | 450 | V |
| Gate-to-Source Voltage | V _{GSS} | | ±30 | V |
| Drain Current (DC) | I _D | | 3 | Α |
| Drain Current (Pulse) | I _{DP} | PW≤10μs, duty cycle≤1% | 12 | Α |
| Allowable Power Dissipation | D- | Tc=25°C | 50 | W |
| | PD | AND LAND VALUE | 1.75 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | LIMI WALLEY | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|---------------------|--|---------|-----|------|------|
| | | | min | typ | max | |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | I _D =1mA, V _{GS} =0 | 450 | | | V |
| Zero-Gate Voltage Drain Current | I _{DSS} | V _{DS} =450V, V _{GS} =0 | | | 1.0 | mA |
| Gate-to-Source Leakage Current | IGSS | $V_{GS}=\pm30V$, $V_{DS}=0$ | | | ±100 | nA |
| Cutoff Voltage | VGS(off) | V _{DS} =10V, I _D =1mA | 2.0 | | 3.0 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =1.5A | 1.0 | 2.0 | | S |
| Static Drain-to-Source ON-State Resistance | R _{DS(on)} | I _D =1.5A, V _{GS} =10V | At At | 2.0 | 2.6 | Ω |

(Note) Be careful in handling the 2SK1439 because it has no protection diode between gate and source.

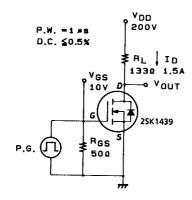
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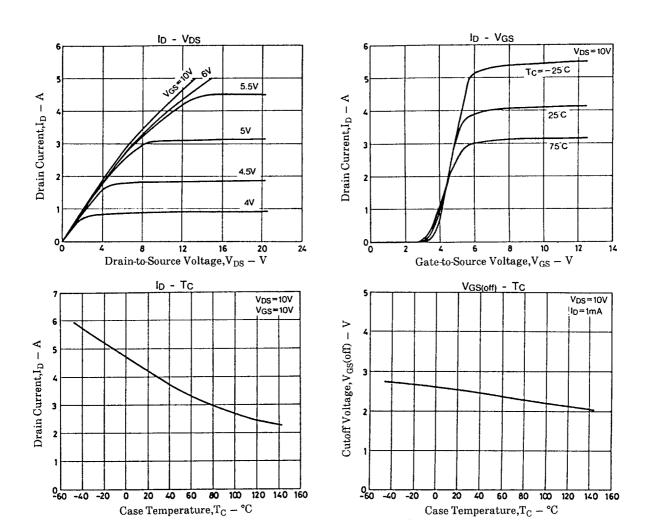
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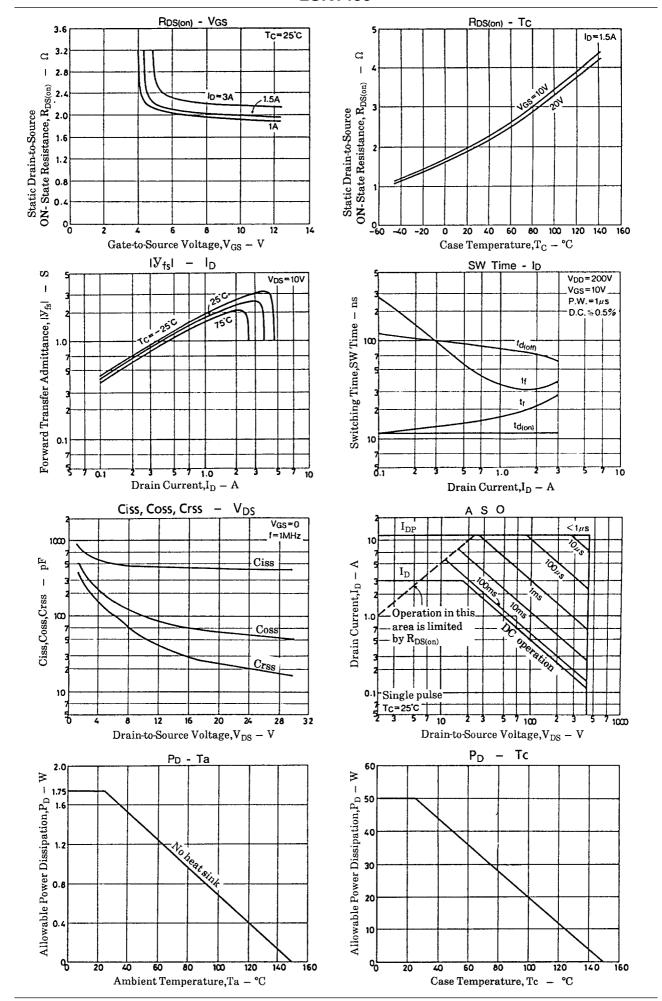
Continued from preceding page.

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|------------------------------|---------------------|---|---------|-----|-----|------|
| | | | min | typ | max | |
| Input Capacitance | Ciss | V _{DS} =20V, f=1MHz | | 400 | | pF |
| Output Capacitance | Coss | V _{DS} =20V, f=1MHz | | 60 | | pF |
| Reverse Transfer Capacitance | Crss | V _{DS} =20V, f=1MHz | | 25 | | pF |
| Turn-ON Delay Time | t _d (on) | I_{D} =1.5A, V_{GS} =10V, V_{DD} =200V, R_{GS} =50 Ω | | 12 | | ns |
| Rise Time | t _r | I_{D} =1.5A, V_{GS} =10V, V_{DD} =200V, R_{GS} =50 Ω | | 20 | | ns |
| Turn-OFF Delay Time | t _{d(off)} | I_{D} =1.5A, V_{GS} =10V, V_{DD} =200V, R_{GS} =50 Ω | | 80 | | ns |
| Fall Time | t _f | I_{D} =1.5A, V_{GS} =10V, V_{DD} =200V, R_{GS} =50 Ω | | 35 | | ns |
| Diode Forward Voltage | V _{SD} | I _S =3A, V _{GS} =0 | | | 1.8 | V |

Switching Time Test Circuit







2SK1439

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